

Description

The DFS06HF12EZC1 is a Half Bridge SiC MOSFET half bridge Power Module. It integrates high performance SiC MOSFET chips designed for the applications such as Solar Inverter, UPS, Fuel cell- DC/DC converter, Energy storage Systems.



Features

- Blocking voltage:1200V
- 6.5mΩ $R_{ds(on)}$ @ $T_j=25^{\circ}C$
- 200A@ $T_f=90^{\circ}C$
- Low Switching Losses
- 175°C maximum junction temperature
- Si₃N₄ DBC
- Thermistor inside

Applications

- Solar inverter Systems
- Fuel cell-DC/DC converter
- Uninterruptible Power Supplier
- Energy Storage Systems

Circuit diagram

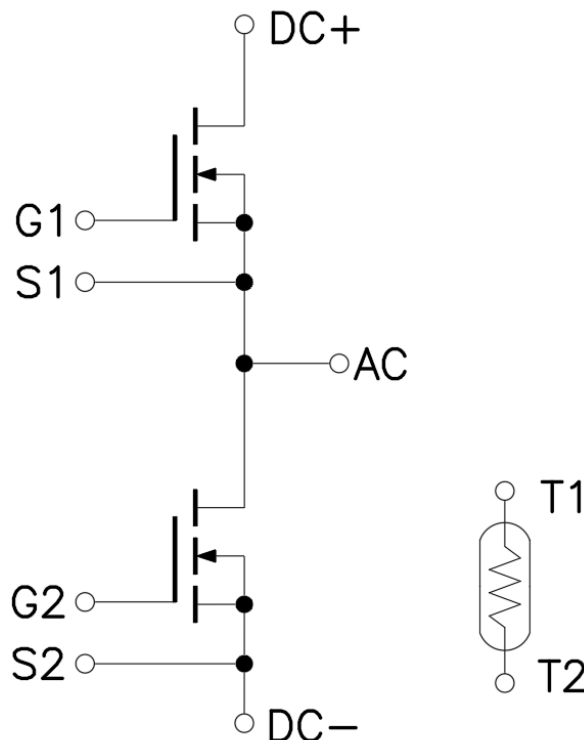


Figure 1. Out drawing & circuit diagram for DFS06HF12EZC1

Pin Configuration and Function Description

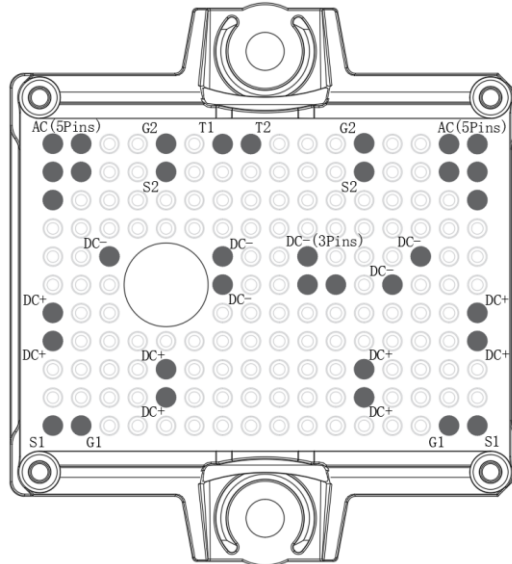


Figure 2. Pin configuration

PIN No.	Symbol	Description
1-5(5pins)	AC	Output terminal of half bridge
6	S2	Low side source signal terminal
7	G2	Low side gate signal terminal
8	T1	Thermistor connection 1
9	T2	Thermistor connection 2
10	S2	Low side source signal terminal
11	G2	Low side gate signal terminal
12-16(5pins)	AC	Output terminal of half bridge
17-24(8pins)	DC –	DC – Bus connection
25-32(8pins)	DC +	DC + Bus connection
33	S1	High side source signal terminal
34	G1	High side gate signal terminal
35	G1	High side gate signal terminal
36	S1	High side source signal terminal

Module

Parameter	Conditions	Value	Unit
Isolation voltage	RMS, f =50Hz, t =1min	3.4	kV
Clearance	Terminal to Terminal	5	mm
	Terminal to Heatsink	10	mm
Creepage distance	Terminal to Terminal	6.3	mm
	Terminal to Heatsink	12.7	mm
Comparative Tracking Index	-	400	-

Maximum Ratings (T_j=25°C unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V _{DSS}	Drain-Source Voltage	G-S Short	1200	V
V _{GSS}	G-S Voltage	D-S Short, Note1	-10 to 20	V
I _{DS}	DC Continuous Drain Current	T _f =90°C	200	A
I _{SD}	Source (Body diode) Current	T _f =90°C, with ON signal	200	A
I _{DP}	Drain Pulse Current, Peak	Less than 1ms, Note2	400	A
T _j	junction temperature	-	-40 to 175	°C
T _{stg}	Storage temperature	-	-40 to 125	°C

Note1: Recommended Operating Value, -5V/+15V.

Note2: Pulse width limited by maximum junction temperature

NTC characteristics

Symbol	Parameter	Condition	Value			Unit
			Min.	Typ.	Max.	
R ₂₅	Resistance	T _C =25°C	-	5	-	kΩ
ΔR/R	Deviation of R100	T _C =100°C, R ₁₀₀ =493Ω	5	-	5	%
P ₂₅	Power dissipation	T _C =25°C	-	-	20	mW
B _{25/50}	B-value	R ₂ =R ₂₅ exp [B _{25/50} (1/T ₂ - 1/(298,15 K))]	-	3375	-	K
B _{25/80}	B-value	R ₂ =R ₂₅ exp [B _{25/80} (1/T ₂ - 1/(298,15 K))]	-	3411	-	K
B _{25/100}	B-value	R ₂ =R ₂₅ exp [B _{25/100} (1/T ₂ - 1/(298,15 K))]	-	3433	-	K

MOSFET Electrical characteristics (T_j=25°C unless otherwise specified, chip)

Symbol	Item	Condition	Value			Unit	
			Min.	Typ.	Max		
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =300uA	1200	-	-	V	
I _{DSS}	Zero gate voltage drain Current	V _{DS} =1200V, V _{GS} =0V	-	3	-	μA	
V _{GS(th)}	Gate-source threshold Voltage	I _D =105mA, V _{DS} =V _{GS} , T _j =25°C	1.8	2.7	-	V	
		I _D =105mA, V _{DS} =V _{GS} , T _j =175°C	-	2.05	-	V	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =20V, V _{DS} =0V, T _j =25°C	-	300	-	nA	
R _{DS(on)} (Chip)	Static drain-source On-state resistance	I _D =200A V _{GS} =15V					
		T _j =25°C	-	6.5	8.6	mΩ	
		T _j =175°C	-	9.6	-	mΩ	
V _{DS(on)} (Chip)	Static drain-source On-state Voltage	I _D =200A V _{GS} =15V					
		T _j =25°C	-	1.30	1.72	V	
		T _j =175°C	-	1.92	-	V	
C _{iss}	Input Capacitance	V _D =800V, V _{GS} =0V	-	17.4	-	nF	
C _{oss}	Output Capacitance	f =1MHz, V _{AC} =25mV	-	0.528	-	nF	
C _{rss}	Reverse transfer Capacitance		-	0.042	-	nF	
Q _G	Total gate charge	V _{DD} =800V, I _D =180A, V _{GS} =-5/+15V	-	540	-	nC	
R _{Gint}	Internal Gate Resistance	f =1Mhz, V _{AC} =25mV	-	0.43	-	Ω	
t _{d(on)}	Turn-on delay time	V _{DD} =600V I _D =200A V _{GS} =-5/+15V R _G =3.3Ω Inductive load switching operation	T _j =25°C	-	31	-	ns
			T _j =150°C	-	28	-	
t _r	Rise time		T _j =25°C	-	18	-	ns
			T _j =150°C	-	18	-	
t _{d(off)}	Turn-off delay time		T _j =25°C	-	101	-	ns
			T _j =150°C	-	119	-	
t _f	Fall time		T _j =25°C	-	38	-	ns
			T _j =150°C	-	42	-	
E _{on}	Turn-on power dissipation		T _j =25°C	-	4.45	-	mJ
			T _j =150°C	-	4.82	-	
E _{off}	Turn-off power dissipation	T _j =25°C	-	2.01	-	mJ	
		T _j =150°C	-	2.22	-		
R _{th(j-c)}	FET Thermal Resistance	Junction to Case/MOSFET	-	0.1	-	K/W	
R _{th(c-f)}	Contact thermal resistance	With thermal conductive grease /MOSFET	-	0.12	-	K/W	

Assumes Thermal Conductivity of grease is 2.8 W/m · K and thickness is 50um.

Body Diode Electrical characteristics (T_j=25°C unless otherwise specified, chip: Target)

Symbol	Item	Condition	Value			Unit	
			Min.	Typ.	Max.		
V _{SD}	Body Diode Forward Voltage	V _{GS} = -5V I _{SD} = 200A	T _j = 25°C	-	5.4	-	V
			T _j = 150°C	-	5.0	-	
T _{rr}	Reverse recovery time	V _{DD} = 600V I _D = 200A	T _j = 25°C	-	56	-	ns
			T _j = 150°C	-	48	-	
Q _{rr}	Reverse recovery charge	V _{GS} = -5/+15V R _G = 3.3Ω	T _j = 25°C	-	3.03	-	μC
			T _j = 150°C	-	6.21	-	
E _{rr}	Diode switching power dissipation	Inductive load switching operation	T _j = 25°C	-	0.92	-	mJ
			T _j = 150°C	-	1.86	-	

Test Conditions

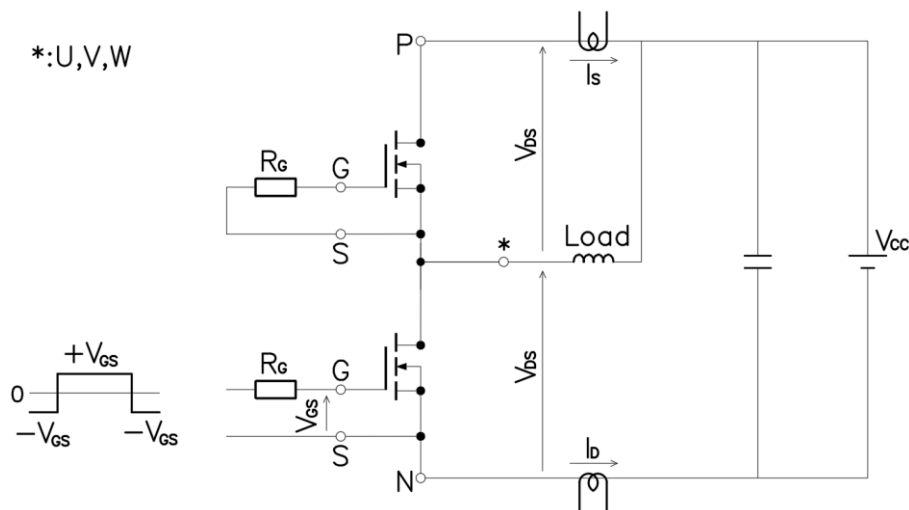


Figure 3. Switching time measure circuit

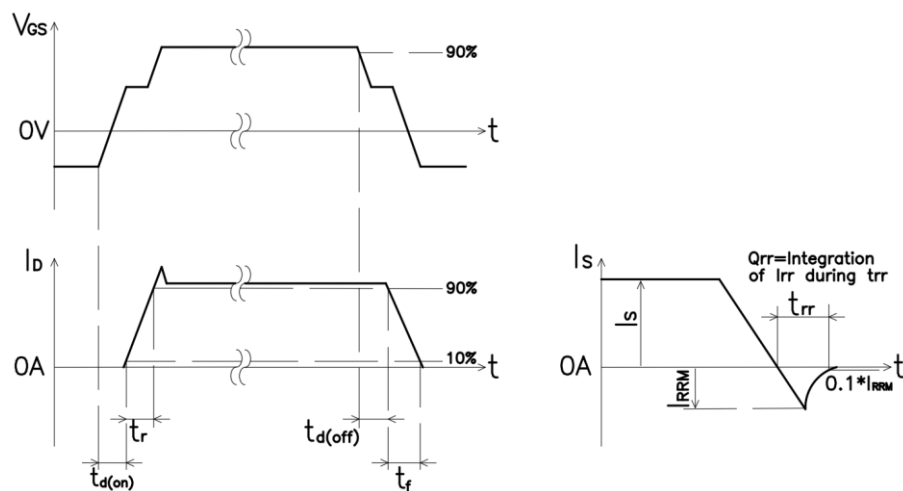


Figure 4. Switching time definition

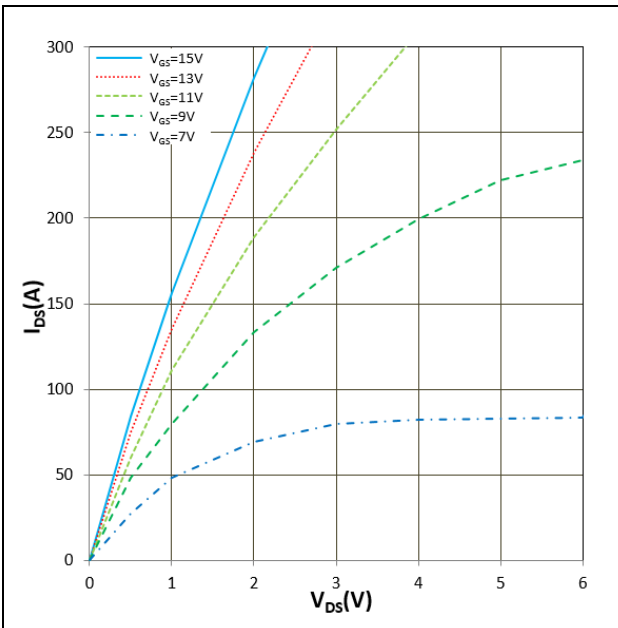


Figure 5. I_{DS} vs V_{DS}
 $T_j = 25^\circ\text{C}$, V_{GS} parameter

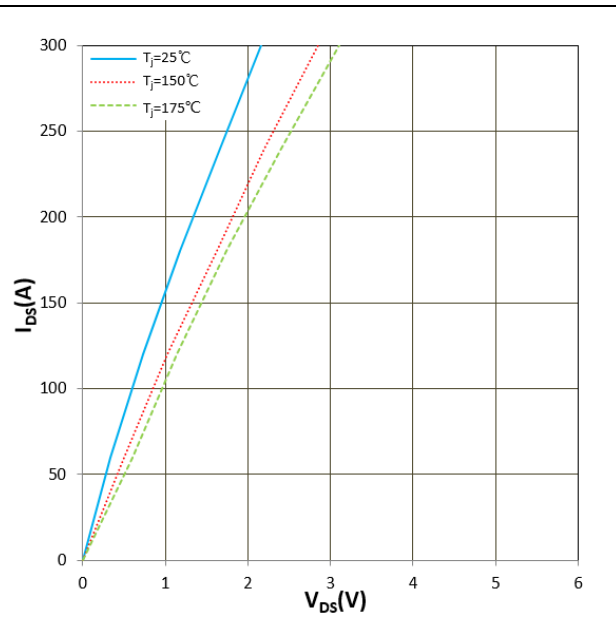


Figure 6. I_{DS} vs V_{DS}
 $V_{GS} = +15\text{V}$

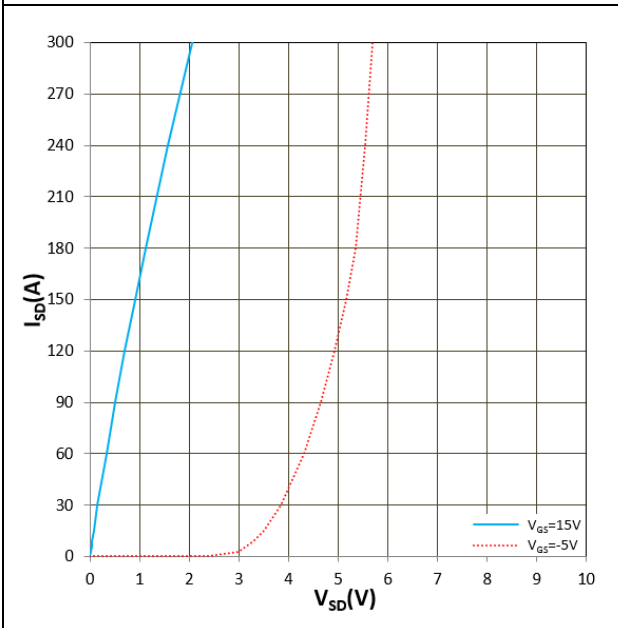


Figure 7. I_{SD} vs V_{SD} (V_F)
 $T_j = 25^\circ\text{C}$, V_{GS} parameter

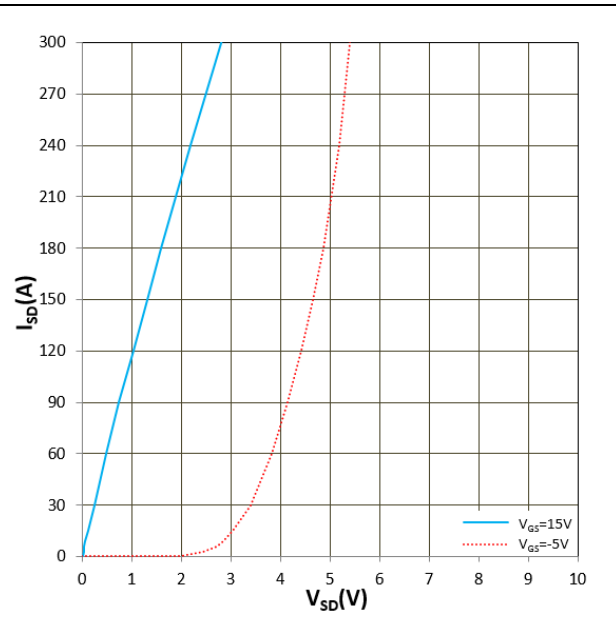


Figure 8. I_{SD} vs V_{SD} (V_F)
 $T_j = 175^\circ\text{C}$, V_{GS} parameter

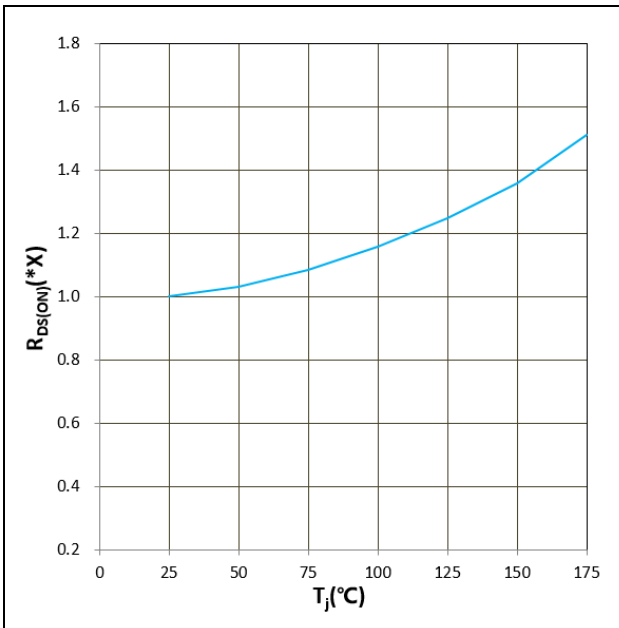


Figure 9. $R_{DS(ON)}$ vs T_j
 $V_{GS} = +15V, I_D = 200A, 1.0X = 6.5m\Omega$

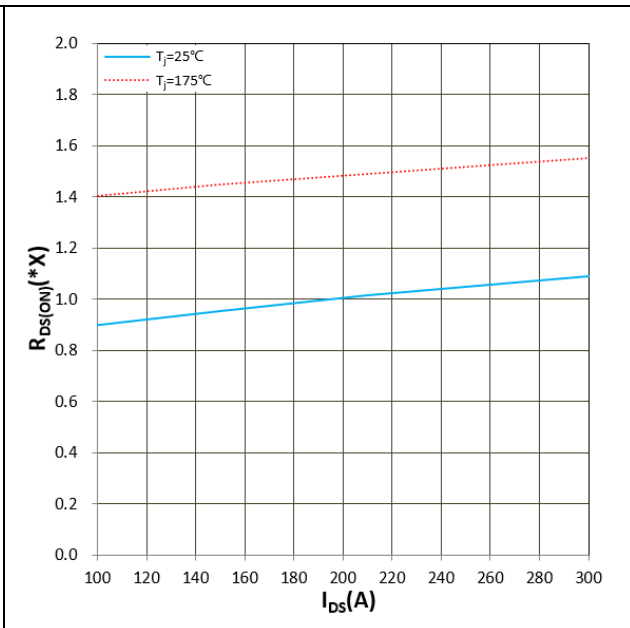


Figure 10. $R_{DS(ON)}$ vs I_{DS}
 $V_{GS} = +15V, 1.0X = 6.5m\Omega$

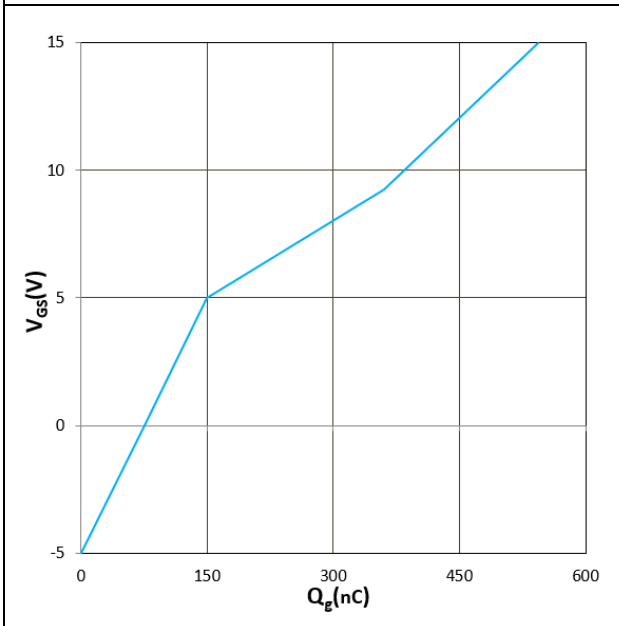


Figure 11. V_{GS} vs Q_g
 $V_{DS} = 800V, I_D = 180A, T_j = 25^\circ C$

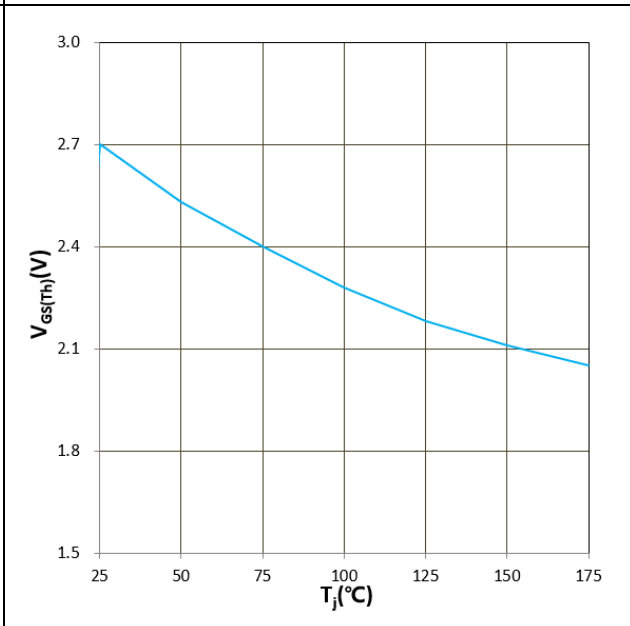


Figure 12. $V_{GS(TH)}$ vs T_j
 $V_{GS} = V_{DS}, I_D = 105mA$

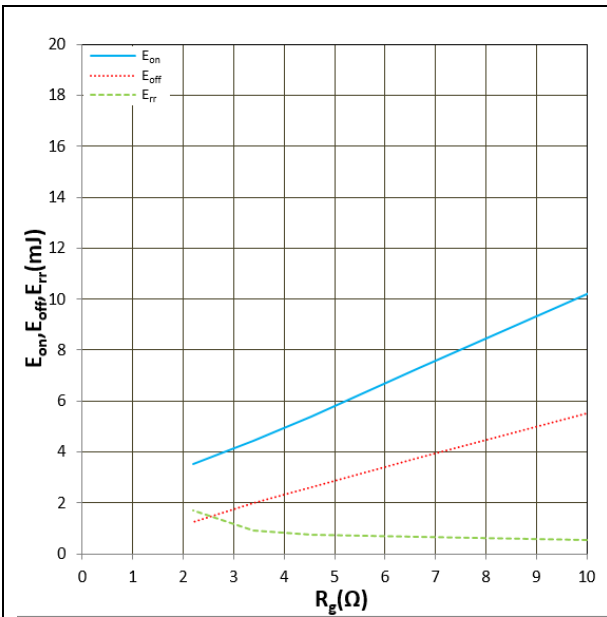


Figure 13. E_{on} , E_{off} , E_{rr} vs R_G
 $T_j = 25^\circ\text{C}$, $V_{CC} = 600\text{V}$, $I_D = 200\text{A}$, $V_{GS} = -5\text{V}/+15\text{V}$
 Inductive Load

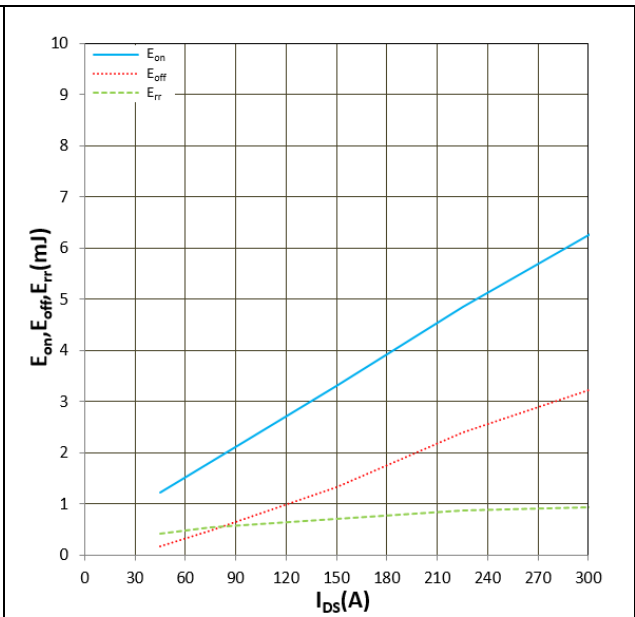


Figure 14. E_{on} , E_{off} , E_{rr} vs I_{Ds}
 $T_j = 25^\circ\text{C}$, $V_{CC} = 600\text{V}$, $R_G = 3.3\Omega$, $V_{GS} = -5\text{V}/+15\text{V}$
 Inductive Load

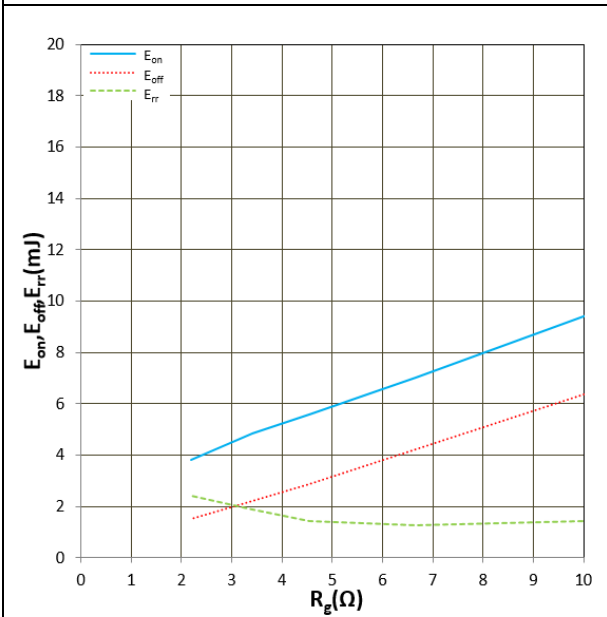


Figure 15. E_{on} , E_{off} , E_{rr} vs R_G
 $T_j = 150^\circ\text{C}$, $V_{CC} = 600\text{V}$, $I_D = 200\text{A}$, $V_{GS} = -5\text{V}/+15\text{V}$
 Inductive Load

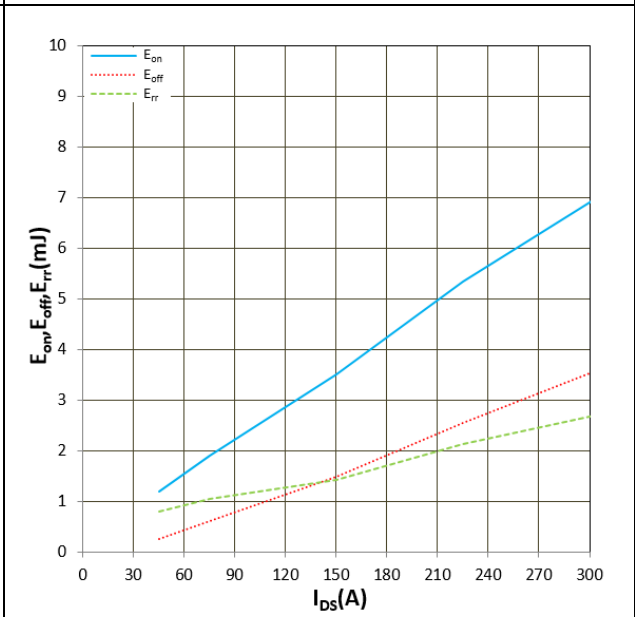
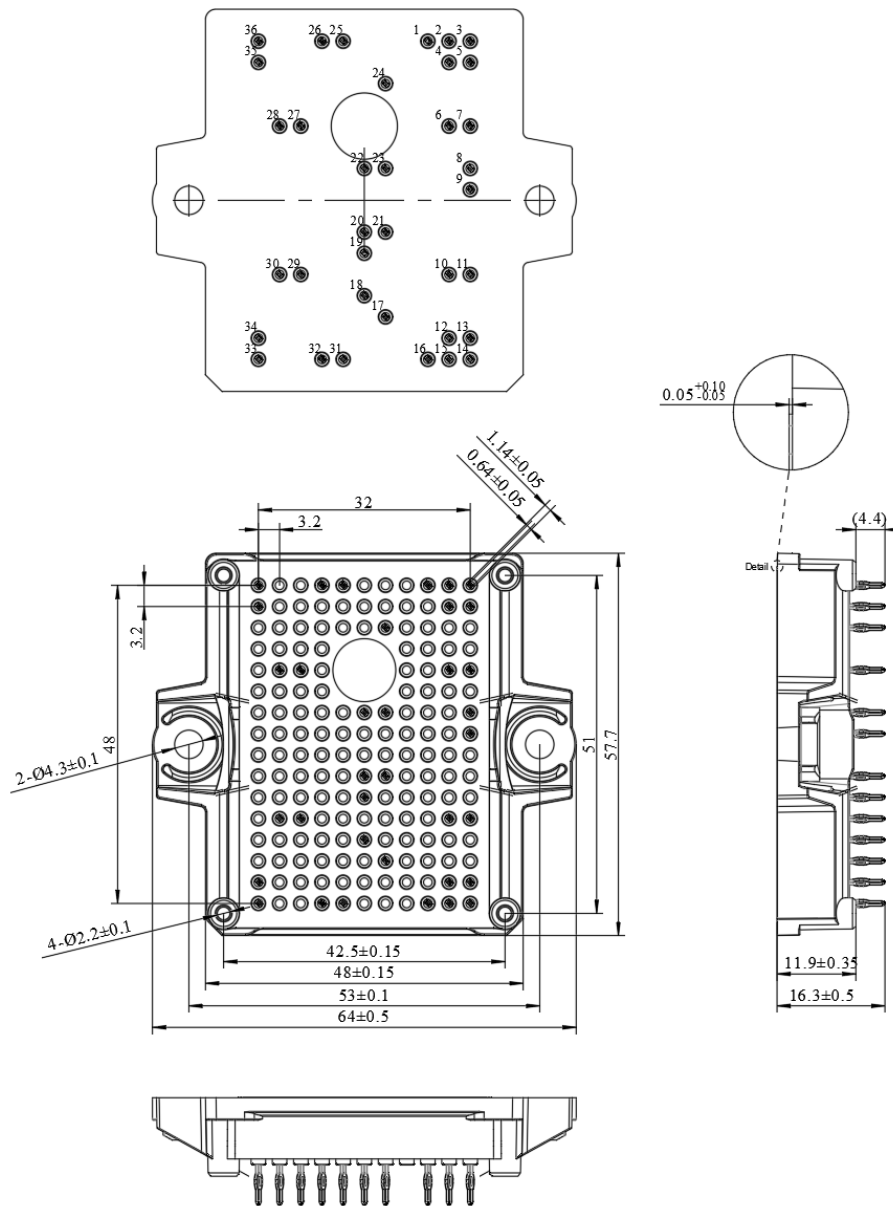


Figure 16. E_{on} , E_{off} , E_{rr} vs I_{Ds}
 $T_j = 150^\circ\text{C}$, $V_{CC} = 600\text{V}$, $R_G = 3.3\Omega$, $V_{GS} = -5\text{V}/+15\text{V}$
 Inductive Load

Package dimensions



Pin	X	Y
1	25,6	48
2	28,8	48
3	32	48
4	28,8	44,8
5	32	44,8
6	28,8	35,2
7	32	35,2
8	32	28,8
9	32	25,6
10	28,8	12,8
11	32	12,8
12	28,8	3,2
13	32	3,2
14	32	0
15	28,8	0
16	25,6	0
17	19,2	6,4
18	16	9,6
19	16	16
20	16	19,2
21	19,2	19,2
22	16	28,8
23	19,2	28,8
24	19,2	41,6
25	12,8	48
26	9,6	48
27	6,4	35,2
28	3,2	35,2
29	6,4	12,8
30	3,2	12,8
31	12,8	0
32	9,6	0
33	0	0
34	0	3,2
35	0	44,8
36	0	48

Unit: mm

IMPORTANT NOTICE

This product data sheet describes the characteristics of this product for which a warranty is granted. Any such warranty is granted exclusively under the terms and conditions of the supply agreement. There will be no guarantee or of any kind for the product and its characteristics.

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